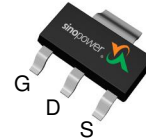


N-Channel Enhancement Mode MOSFET

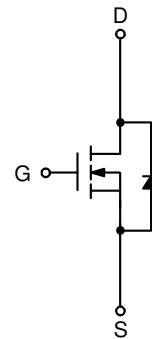
Features

- 100V/8A,
 $R_{DS(ON)} = 29m\Omega(max.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 33m\Omega(max.) @ V_{GS} = 4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

Pin Description



Top View SOT-223

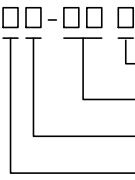
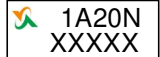


N-Channel MOSFET

Applications

- Power Management in DC/DC Converter.

Ordering and Marking Information

SM1A20NS □□-□□ □ 	Package Code V : SOT-223 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel (2500ea/reel) Assembly Material G : Halogen and Lead Free Device
SM1A20NS V: 	XXXXX - Lot Code

Note: SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
I_S	Diode Continuous Forward Current	$T_A = 25^\circ\text{C}$	A
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	A
		$T_A = 70^\circ\text{C}$	
I_{DM}^a	Pulsed Drain Current	$T_A = 25^\circ\text{C}$	A
P_D	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	W
		$T_A = 70^\circ\text{C}$	
$R_{\theta JA}^c$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$^\circ\text{C/W}$
		Steady State	$^\circ\text{C/W}$
I_{AS}^b	Avalanche Current, Single pulse ($L=0.5\text{mH}$)	18	A
E_{AS}^b	Avalanche Energy, Single pulse ($L=0.5\text{mH}$)	81	mJ

Note a: Pulse width is limited by maximum junction temperature.

b: UIS tested and pulse width are limited by maximum junction temperature 150°C (initial temperature $T_J = 25^\circ\text{C}$)

c: Surface Mounted on 1in^2 pad area,

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_{DS}=250\mu\text{A}$	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=80\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$T_J=85^\circ\text{C}$	-	-	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	1	2	3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$	-	-	± 100	nA
$R_{DS(ON)}^d$	Drain-Source On-state Resistance	$V_{GS}=10\text{V}, I_{DS}=8\text{A}$	-	24	29	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_{DS}=6\text{A}$	-	25	33	$\text{m}\Omega$

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

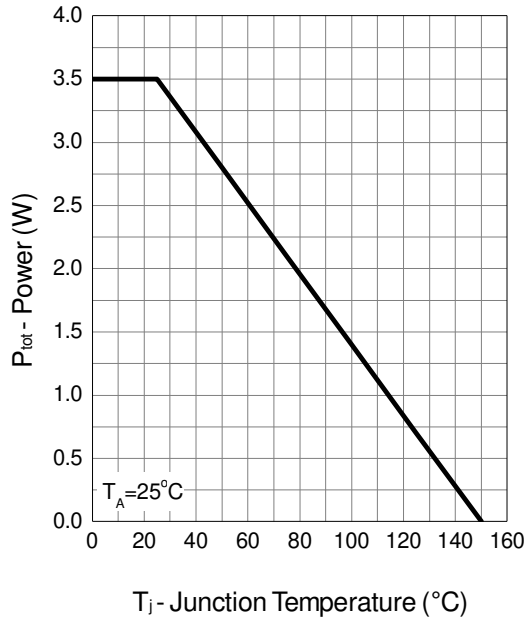
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Diode Characteristics						
V_{SD}^c	Diode Forward Voltage	$I_{SD}=5A, V_{GS}=0V$	-	0.8	1.3	V
t_{rr}	Reverse Recovery Time	$I_{SD}=5A, dI_{SD}/dt=100A/\mu s$	-	40	-	ns
Q_{rr}	Reverse Recovery Charge		-	70	-	nC
Dynamic Characteristics ^d						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	1.0	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz	-	2400	3120	pF
C_{oss}	Output Capacitance		-	150	-	
C_{rss}	Reverse Transfer Capacitance		-	85	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=30V, R_L=30\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=6\Omega$	-	18	33	ns
t_r	Turn-on Rise Time		-	9	17	
$t_{d(OFF)}$	Turn-off Delay Time		-	56	101	
t_f	Turn-off Fall Time		-	14	26	
Gate Charge Characteristics ^d						
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=4.5V,$ $I_{DS}=8A$	-	23	-	nC
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=10V,$ $I_{DS}=8A$	-	50	65	
Q_{gs}	Gate-Source Charge		-	9	-	
Q_{gd}	Gate-Drain Charge		-	9	-	

Note d: Pulse test; pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.

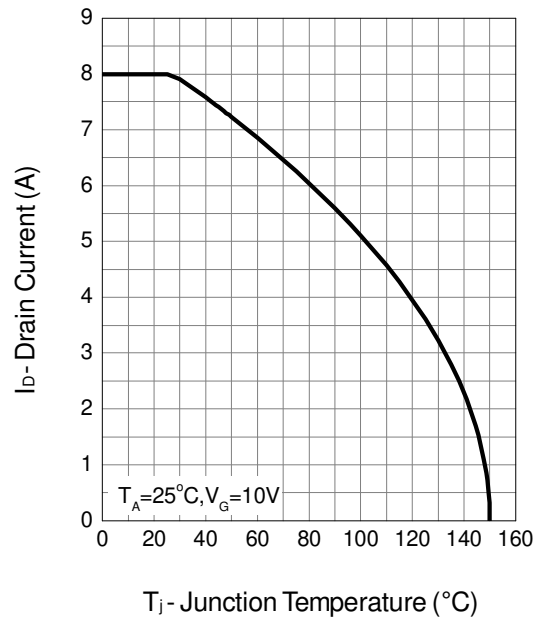
e: Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

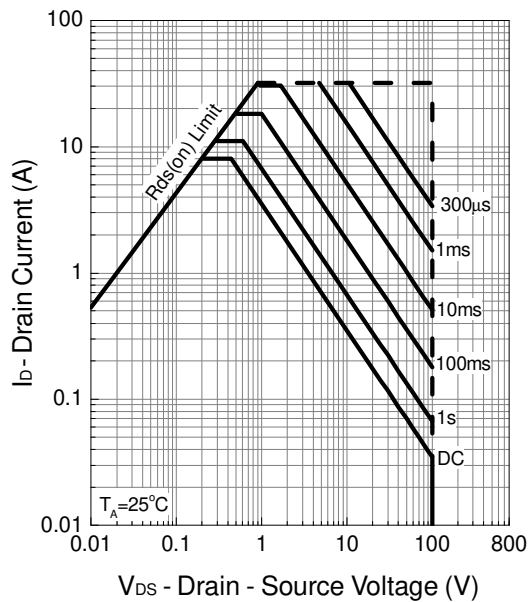
Power Dissipation



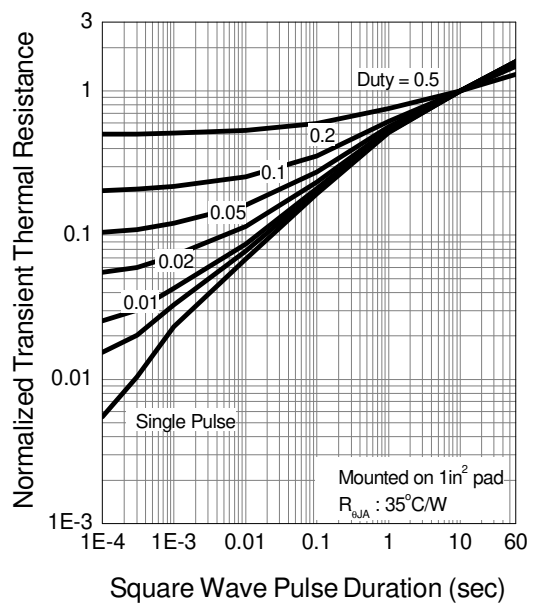
Drain Current



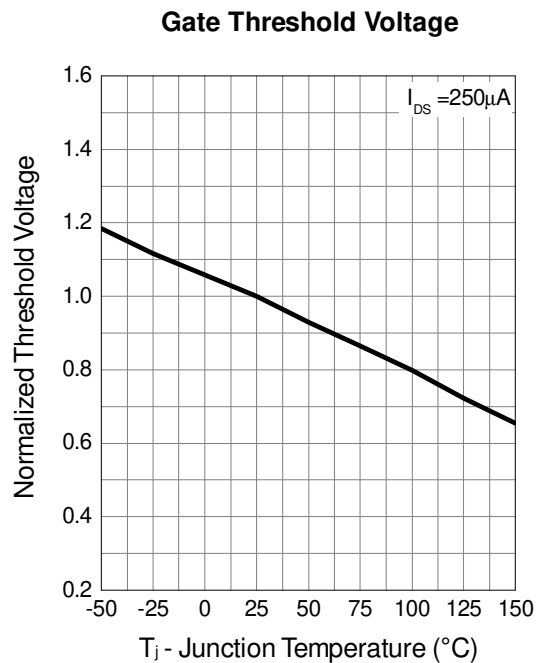
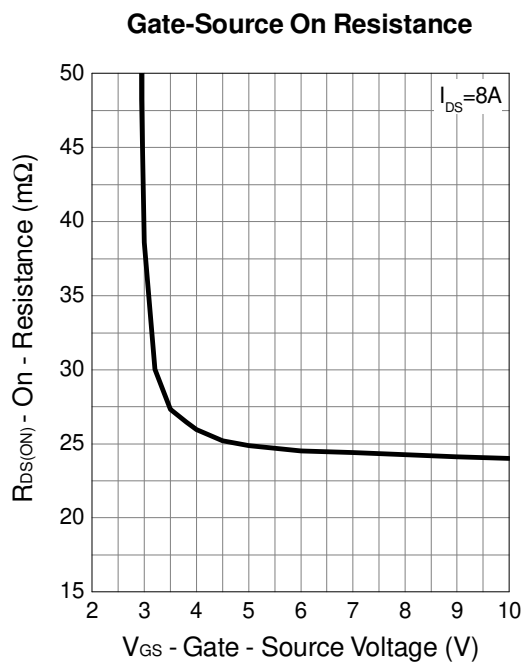
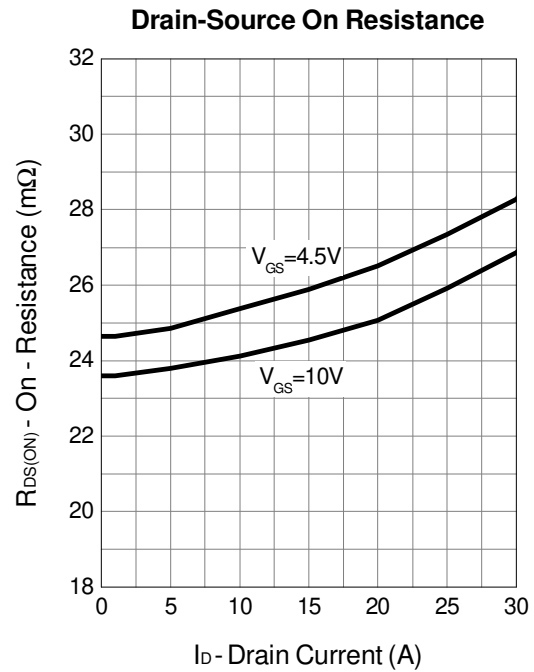
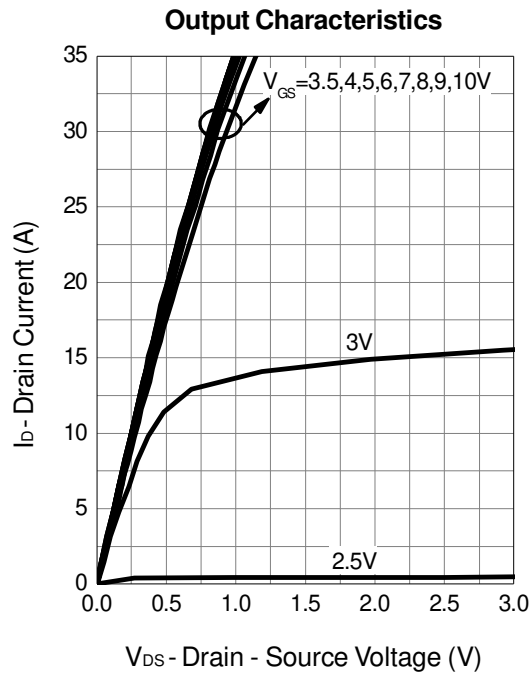
Safe Operation Area



Thermal Transient Impedance

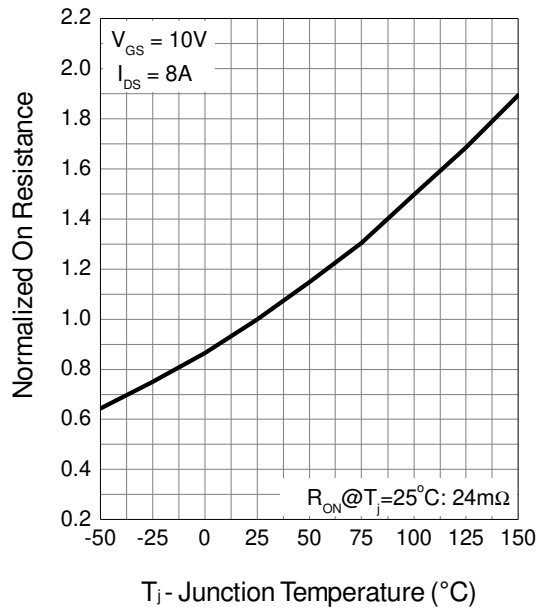


Typical Operating Characteristics (Cont.)

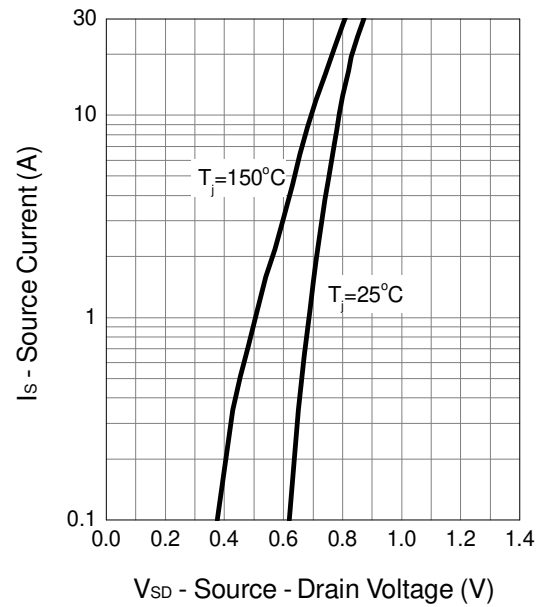


Typical Operating Characteristics (Cont.)

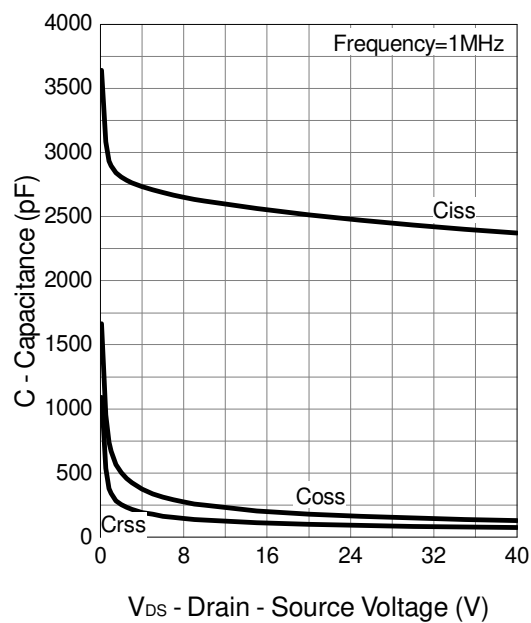
Drain-Source On Resistance



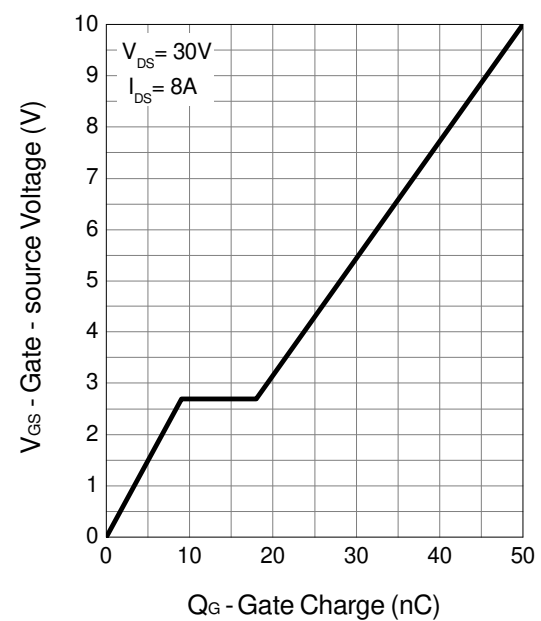
Source-Drain Diode Forward



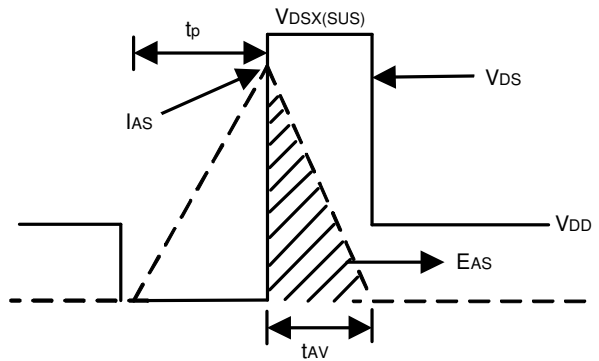
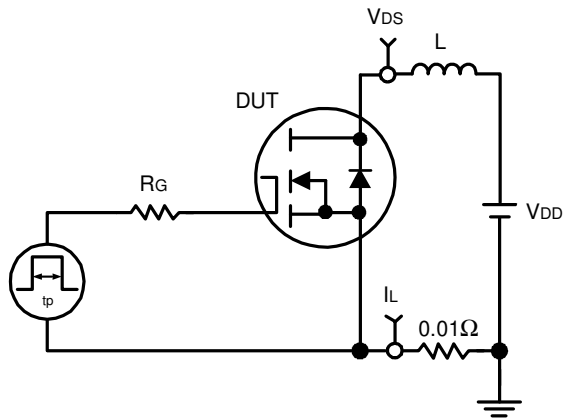
Capacitance



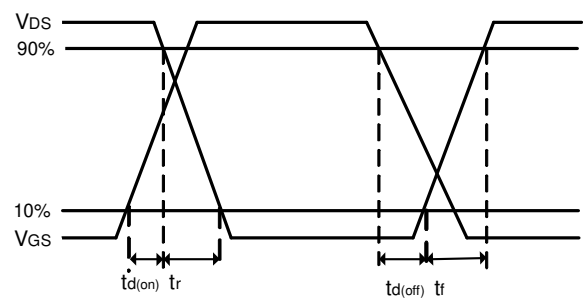
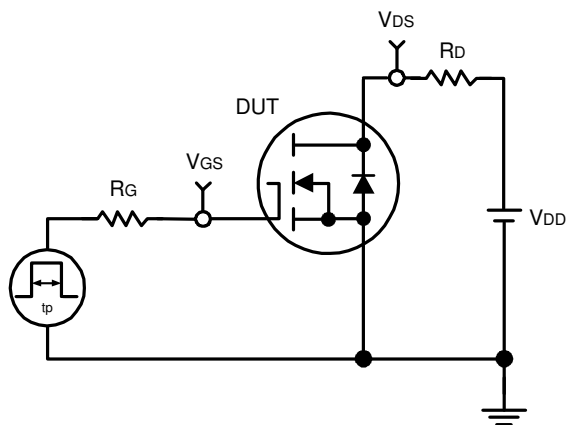
Gate Charge



Avalanche Test Circuit and Waveforms

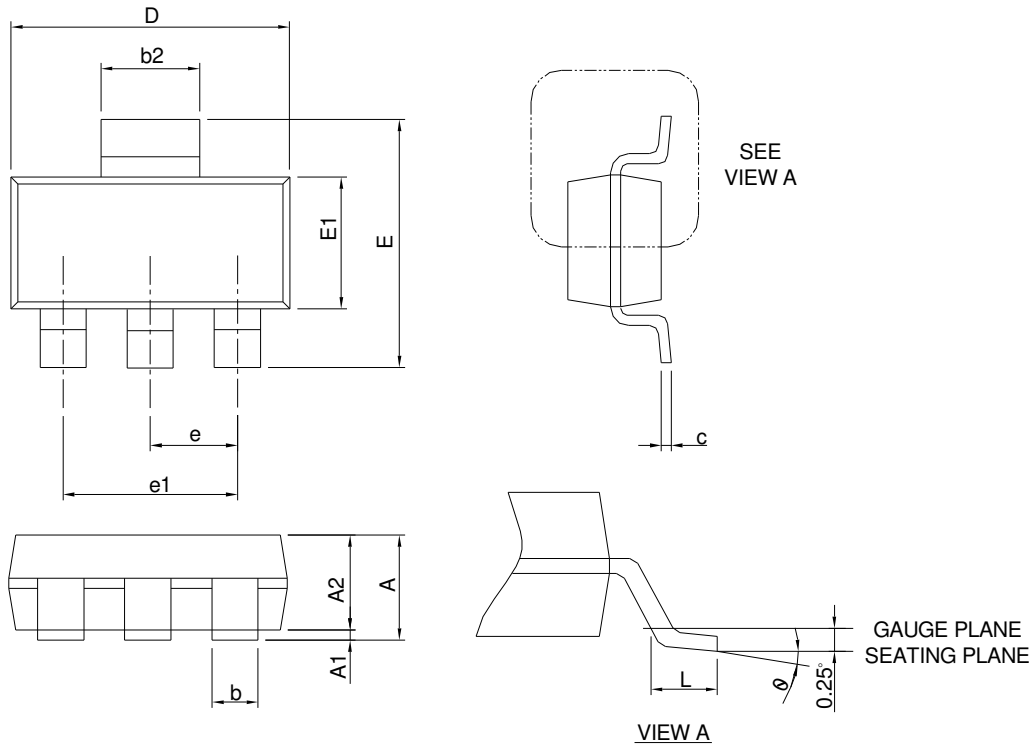


Switching Time Test Circuit and Waveforms



Package Information

SOT-223

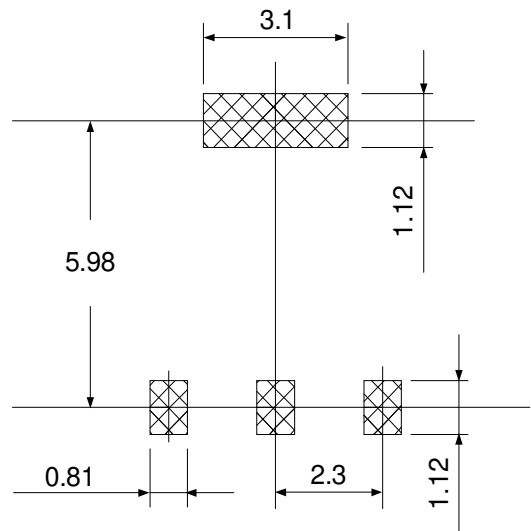


DIMENSIONS	SOT-223			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.80		0.071
A1	0.02	0.10	0.001	0.004
A2	1.50	1.70	0.059	0.067
b	0.66	0.84	0.026	0.033
b2	2.90	3.10	0.114	0.122
c	0.23	0.33	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.30 BSC		0.091 BSC	
e1	4.60 BSC		0.181 BSC	
L	0.75		0.030	
θ	0°	10°	0°	10°

Note : 1. Follow from JEDEC TO-261 AA.

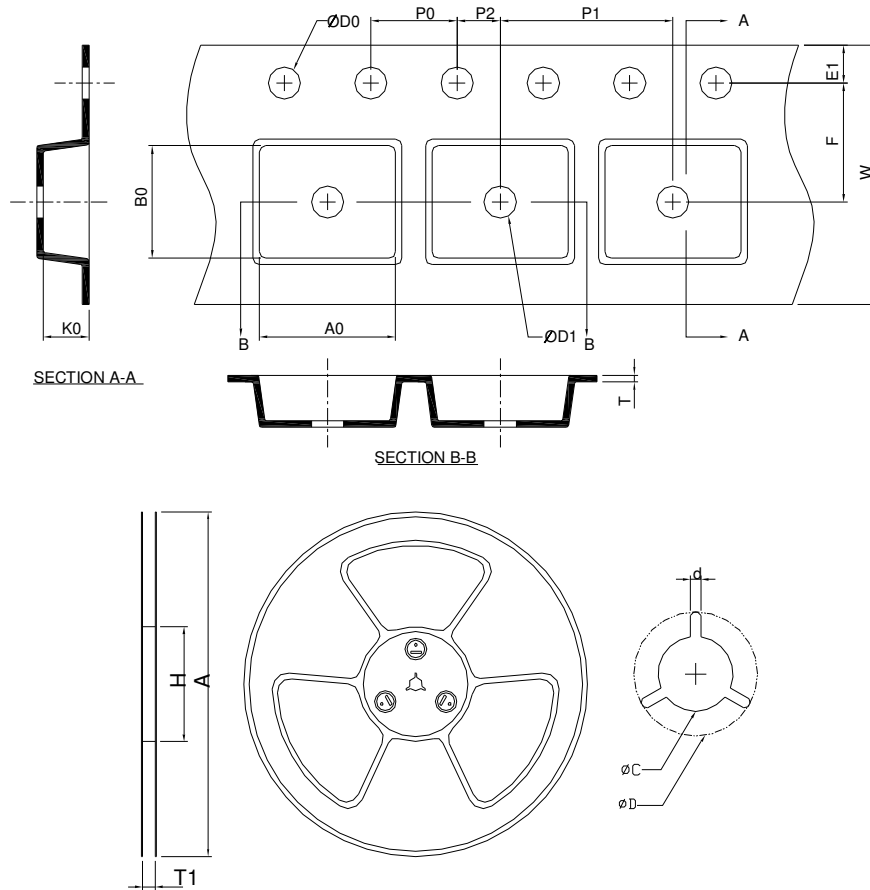
2. Dimension D and E1 are determined at the outermost extremes of the plastic exclusive of mold flash, tie bar burrs, gate burrs, and interlead flash, but including any mismatch between the top and bottom of the plastic body.

RECOMMENDED LAND PATTERN



UNIT: mm

Carrier Tape & Reel Dimensions

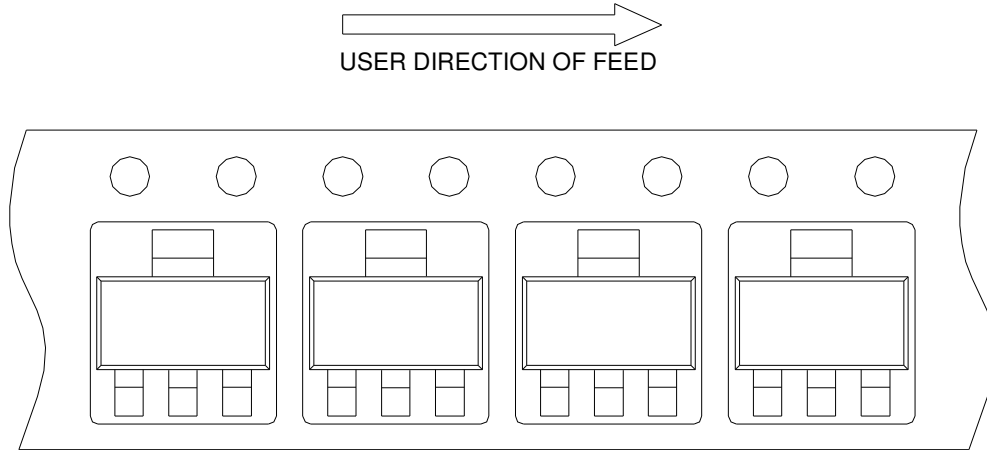


Application	A	H	T1	C	d	D	W	E1	F
SOT-223	320.0±2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.00±0.30	1.75±0.10	5.50±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.00±0.10	8.00±0.10	2.00±0.50	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.90±0.20	7.50±0.20	2.10±0.20

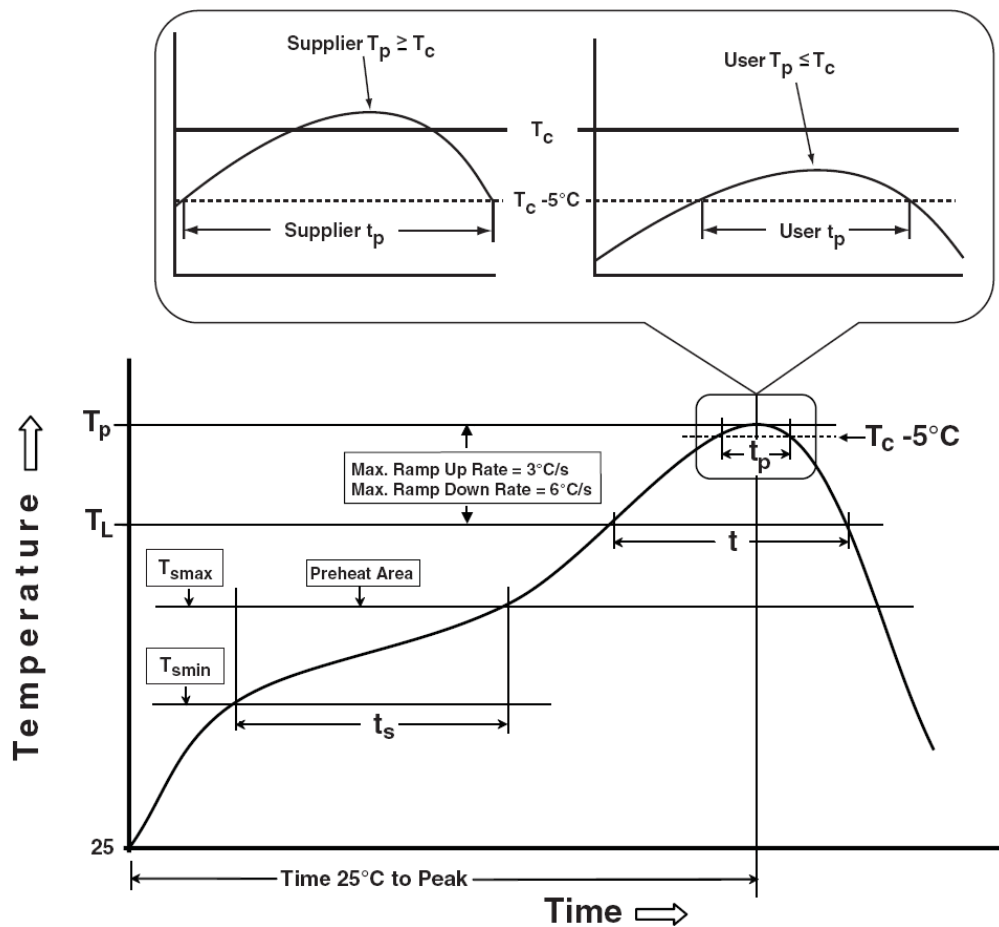
(mm)

Taping Direction Information

SOT-223



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

Sinopower Semiconductor, Inc.

5F, No. 6, Dusing 1St Rd., Hsinchu Science Park,

Hsinchu, 30078, Taiwan

TEL: 886-3-5635818 Fax: 886-3-5642050